2SD2179

Silicon NPN epitaxial planer type

For low-frequency output amplification Complementary to 2SB1446

Features

- Low collector to emitter saturation voltage V_{CE(sat)}.
- Complementary pair with 2SB1446.
- Allowing supply with the radial taping.

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|-------------------|------|
| Collector to base voltage | V_{CBO} | 50 | V |
| Collector to emitter voltage | V_{CEO} | 50 | V |
| Emitter to base voltage | $V_{\rm EBO}$ | 5 | V |
| Peak collector current | I_{CP} | 7 | A |
| Collector current | I_{C} | 5 | A |
| Collector power dissipation | P _C * | 1 | W |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T_{stg} | −55 ~ +150 | °C |

^{*1} Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25°C)

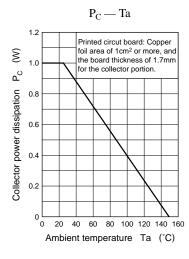
| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|----------------------|---|-----|------|-----|------|
| Collector cutoff current | I_{CBO} | $V_{CB} = 20V, I_E = 0$ | | | 0.1 | μΑ |
| Collector to base voltage | V _{CBO} | $I_C = 10 \mu A, I_E = 0$ | 50 | | | V |
| Collector to emitter voltage | V _{CEO} | $I_C = 1 \text{mA}, I_B = 0$ | 50 | | | V |
| Emitter to base voltage | V _{EBO} | $I_E = 10 \mu A, I_C = 0$ | 5 | | | V |
| F 1 | h _{FE1} *1 | $V_{CE} = 2V, I_C = 500 \text{mA}^{*2}$ | 120 | | 340 | |
| Forward current transfer ratio | h _{FE2} | $V_{CE} = 2V, I_C = 2.5A^{*2}$ | 60 | | | |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = 2A, I_B = 100 \text{mA}^{*2}$ | | 0.19 | 0.3 | V |
| Base to emitter saturation voltage | V _{BE(sat)} | $I_C = 2A$, $I_B = 100 \text{mA}^{*2}$ | | 0.85 | 1.2 | V |
| Transition frequency | f_T | $V_{CB} = 10V, I_E = -50mA, f = 200MHz$ | | 80 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10V, I_E = 0, f = 1MHz$ | | 60 | 70 | pF |

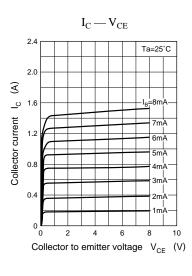
^{*2} Pulse measurement

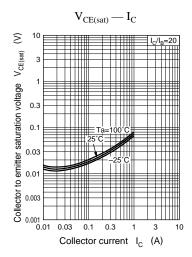
^{*1}hFE1 Rank classification

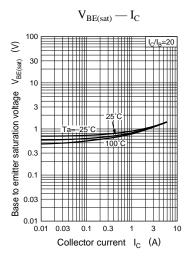
| Rank | R | S |
|------------------|-----------|-----------|
| h _{FE1} | 120 ~ 240 | 170 ~ 340 |

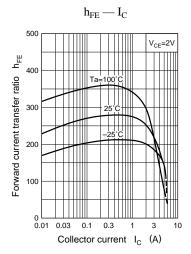
Transistor 2SD2179

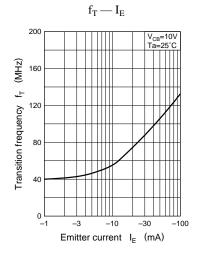


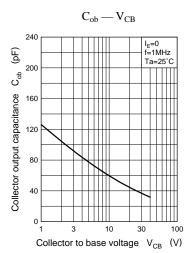












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